

Thermal Shifts and Electron-Phonon Interactions of 4T_2 and 4T_1 Broad Bands for Ruby

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(Received: 2001-6-25; Revised:)

Abstract: For the first time, by taking into account all the irreducible representations and their components in the electron-phonon interaction (EPI) as well as all the levels and the admixtures of wavefunctions within d^3 electronic configuration, the values of parameters in expressions of Raman and optical-branch terms of thermal shifts (TS) due to EPI for three levels, 4T_2 band and 4T_1 band of ruby have been evaluated; the contributions to TS of 4T_2 and 4T_1 broad bands from thermal expansion have also been calculated; and then, the TS of the peak energies of 4T_2 and 4T_1 broad bands have been calculated. The results are in satisfactory agreement with observed data. The values of single-electron reduced matrix elements representing the strengths of EPI of 4T_2 and 4T_1 bands have respectively been determined. For TS of the peak energies of 4T_2 and 4T_1 bands, it is found that the contribution to TS from the second-order term in EPI Hamiltonian is dominant; TS due to EPI of acoustic branches are over two times as much as those of optical branches, and both of them increase rapidly with temperature; the neighbor-level term is insignificant; the contribution to TS from thermal expansion is specially important, and all the three terms of TS of 4T_2 or 4T_1 band are red shifts.

PACS: 78.20.Nv, 71.70.Ch, 63.20.Mt, 63.20.Kr

Key words: crystal fields, optical spectral bands, electron-phonon interaction, thermal expansion, thermal shift

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